

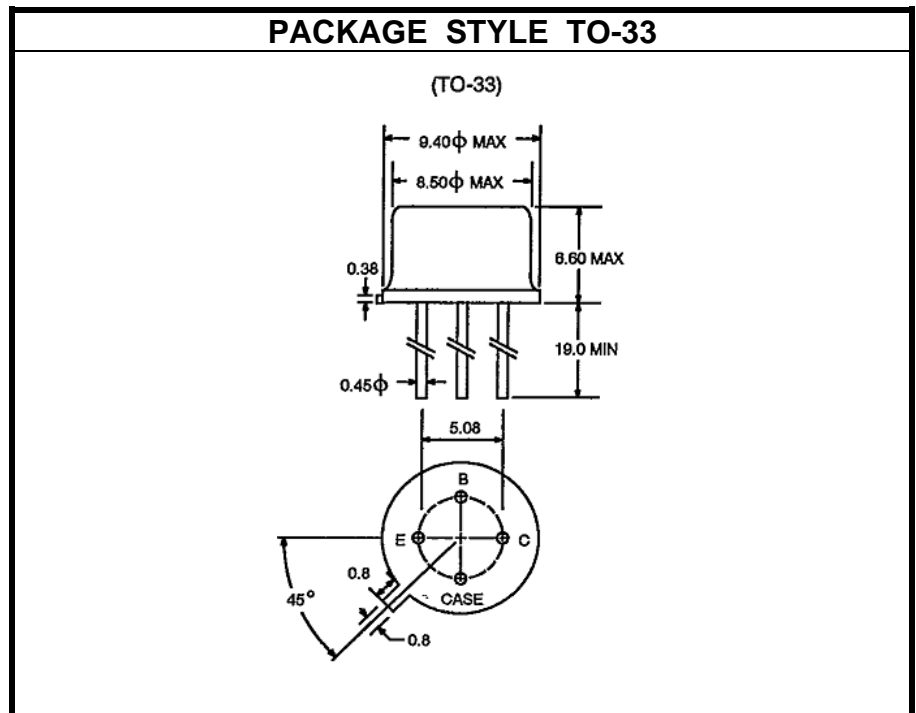
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **2SC2952** is a High Frequency Transistor Designed for General Purpose VHF-UHF Amplifier Applications.

MAXIMUM RATINGS

I_C	250 mA
V_{CE}	30 V
P_{DISS}	3.5 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-65 to +200 $^\circ\text{C}$
T_{STG}	-65 to +200 $^\circ\text{C}$
θ_{JC}	50 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 1.0\text{ mA}$			20			V
BV_{CBO}	$I_C = 100\text{ }\mu\text{A}$			30			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$			3			V
I_{CBO}	$V_{CB} = 20\text{ V}$					10	μA
h_{FE}	$V_{CE} = 10\text{ V}$	$I_C = 80\text{ mA}$		30	80	200	---
f_t	$V_{CE} = 10\text{ V}$	$I_E = 60\text{ mA}$	$f = 200\text{ MHz}$	2800	3300		MHz
C_{CB}	$V_{CB} = 10\text{ V}$		$f = 1.0\text{ MHz}$			2.5	pF
$ S_{21E} ^2$	$V_{CE} = 10\text{ V}$	$I_E = 60\text{ mA}$	$f = 500\text{ MHz}$	8.5			dB
NF	$V_{CE} = 10\text{ V}$	$I_C = 10\text{ mA}$	$f = 500\text{ MHz}$		3.5		dB